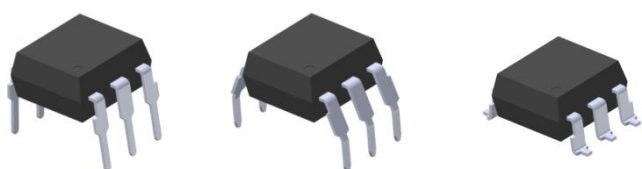


### 6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER CNY17-X Series CNY17F-X Series



#### Features:

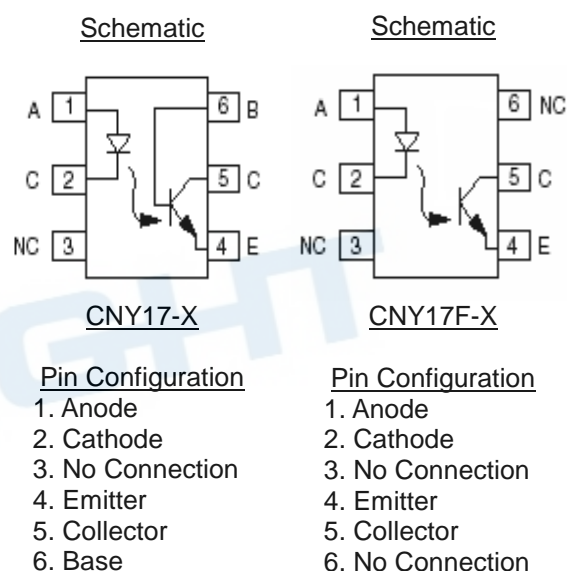
- Current transfer ratios in selected narrow range groups  
CNY17-1, CNY17F-1: 40-80%  
CNY17-2, CNY17F-2: 63-125%  
CNY17-3, CNY17F-3: 100-200%  
CNY17-4, CNY17F-4: 160-320%
- High isolation voltage between input and output  
(Viso = 5000 Vrms)
- Creepage distance > 7.6 mm
- Operating temperature up to +110°C
- The CNY17F-X series offers no external base connection for minimum noise susceptibility
- Compact dual-in-line package
- The product itself will remain within RoHS compliant version
- Compliance with EU REACH
- UL and cUL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved

#### Description

The CNY17-X and CNY17F-X series of devices each consist of an infrared emitting diode optically coupled to a phototransistor. They are packaged in a 6-pin DIP package and available in wide-lead spacing and SMD option.

#### Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs



**Absolute Maximum Ratings (Ta=25°C)**

	Parameter	Symbol	Rating	Unit
Input	Forward current	$I_F$	60	mA
	Peak forward current (t = 10μs)	$I_{FM}$	1	A
	Reverse voltage	$V_R$	6	V
	Power dissipation (T <sub>A</sub> = 25°C)	$P_D$	100	mW
	Derating factor (above 100°C)		3.8	mW/°C
Output	Collector-Emitter voltage	$V_{CEO}$	80	V
	Collector-Base voltage* <sup>1</sup>	$V_{CB0}$	80	V
	Emitter-Collector voltage	$V_{ECO}$	7	V
	Emitter-Base voltage	$V_{EBO}$	7	V
	Power dissipation (T <sub>A</sub> = 25°C)	$P_C$	150	mW
Derating factor (above 100°C)	9.0		mW/°C	
	Total Power Dissipation	$P_{TOT}$	200	mW
	Isolation voltage * <sup>2</sup>	$V_{ISO}$	5000	V rms
	Operating Temperature	$T_{OPR}$	-55 to 110	°C
	Storage Temperature	$T_{STG}$	-55 to 125	°C
	Soldering temperature * <sup>3</sup>	$T_{SOL}$	260	°C

Notes:

\*1 Only for CNY17-X series.

\*2 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 & 3 are shorted together, and pins 4, 5 & 6 are shorted together.

\*3 For 10 seconds.

**Electro-Optical Characteristics (Ta=25°C unless specified otherwise)**

**Input**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward voltage	$V_F$	-	-	1.65	V	$I_F = 60\text{mA}$
Reverse current	$I_R$	-	-	10	$\mu\text{A}$	$V_R = 6\text{V}$
Input capacitance	$C_{in}$	-	18	-	pF	$V = 0, f = 1\text{MHz}$

**Output**

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition
Collector-Base dark current	$I_{CBO}$	-	-	20	nA	$V_{CB} = 10\text{V}, I_F = 0\text{mA}$
Collector-Emitter dark current	$I_{CEO}$	-	-	50	nA	$V_{CE} = 10\text{V}, I_F = 0\text{mA}$
Collector-Emitter breakdown voltage	$BV_{CEO}$	80	-	-	V	$I_C = 1\text{mA}, I_F = 0\text{mA}$
Collector-Base breakdown voltage	$BV_{CBO}$	80	-	-	V	$I_C = 0.1\text{mA}, I_F = 0\text{mA}$
Emitter-Collector breakdown voltage	$BV_{ECO}$	7	-	-	V	$I_E = 0.1\text{mA}, I_F = 0\text{mA}$
Collector-Emitter capacitance	$C_{CE}$	-	8	-	pF	$V_{CE} = 0\text{V}, f = 1\text{MHz}$

\* Typical values at  $T_a = 25^\circ\text{C}$

**Transfer Characteristics**

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition	
Current Transfer Ratio	CNY17-1 CNY17F-1	40	-	80	%	$I_F = 10\text{mA}, V_{CE} = 5\text{V}$	
	CNY17-2 CNY17F-2	63	-	125			
	CNY17-3 CNY17F-3	100	-	200			
	CNY17-4 CNY17F-4	160	-	320			
	CTR						
Current Transfer Ratio	CNY17-1 CNY17F-1	13	-	-	%	$I_F = 1\text{mA}, V_{CE} = 5\text{V}$	
	CNY17-2 CNY17F-2	22	-	-			
	CNY17-3 CNY17F-3	34	-	-			
	CNY17-4 CNY17F-4	56	-	-			
	CTR						
Collector-Emitter saturation voltage	$V_{CE(sat)}$	-	-	0.3	V	$I_F = 10\text{mA}, I_C = 2.5\text{mA}$	
Isolation resistance	$R_{IO}$	$10^{11}$	-	-	$\Omega$	$V_{IO} = 500\text{Vdc}$	
Input-output capacitance	$C_{IO}$	-	0.5	-	pF	$V_{IO} = 0, f = 1\text{MHz}$	
Turn-on time	$T_{on}$	-	10	12	$\mu\text{s}$	$V_{CC} = 10\text{V}, I_C = 2\text{mA}, R_L = 100\Omega$ See Fig. 11	
Turn-off time	$T_{off}$	-	9	12			
Rise time	$T_r$	-	6	10			
Fall time	$T_f$	-	8	10			
Rise time	$T_r$	-	2	10			
Fall time	$T_f$	-	3	10			
Rise time	$T_r$	-	2	10			$V_{CC} = 5\text{V}, I_F = 10\text{mA}, R_L = 75\Omega, \text{ See Fig. 11}$
Fall time	$T_f$	-	3	10			

\* Typical values at  $T_a = 25^\circ\text{C}$

Typical Electro-Optical Characteristics Curves

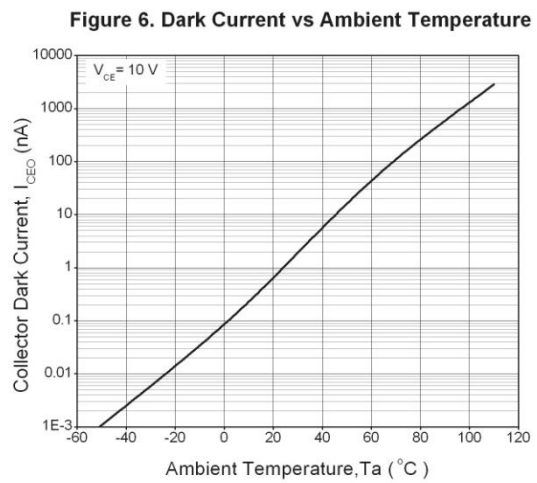
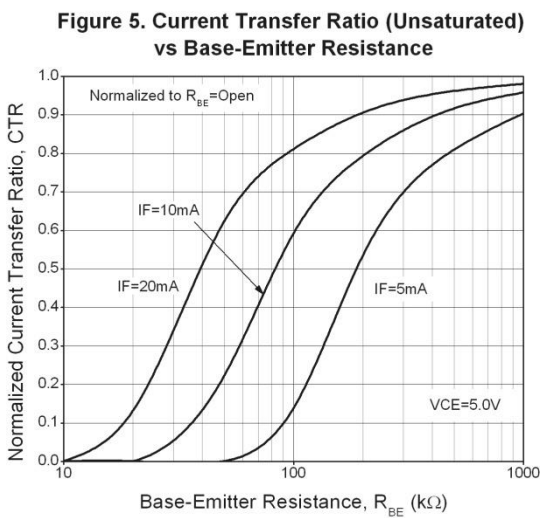
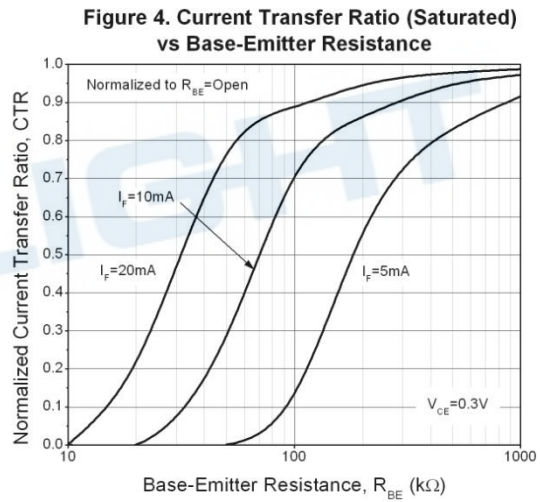
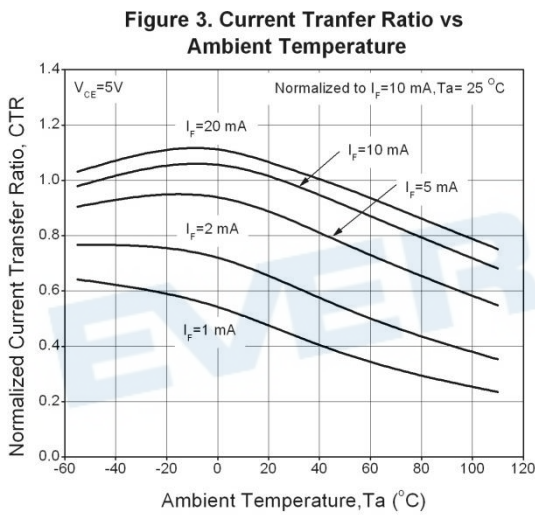
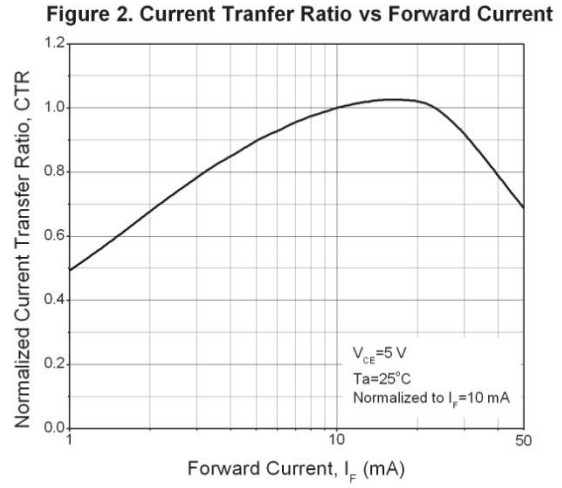
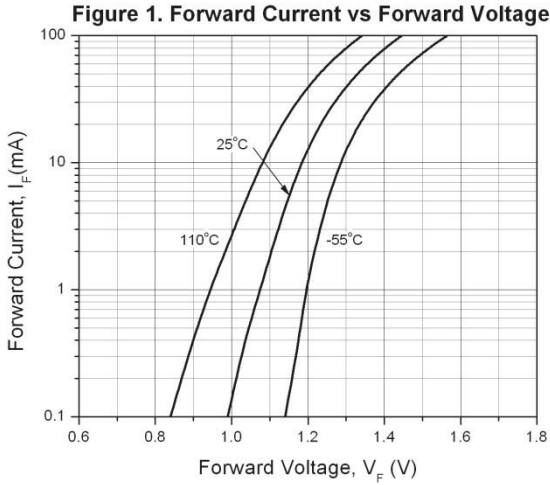


Figure 7. Collector-Emitter Saturation Voltage vs Collector Current

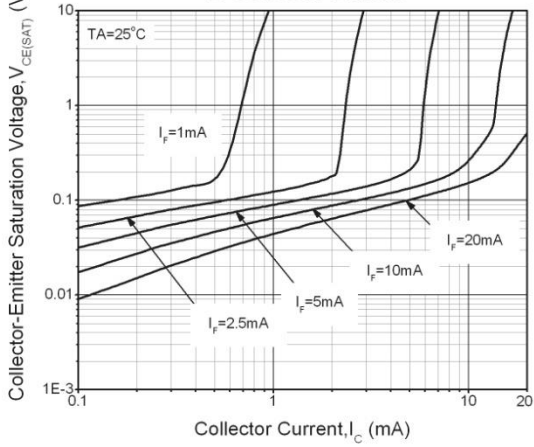


Figure 8. Switching Time vs Load Resistance

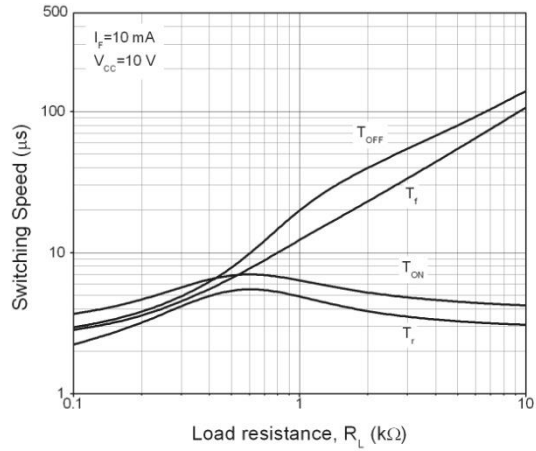


Figure 9. Turn-on Time vs Base-Emitter Resistance

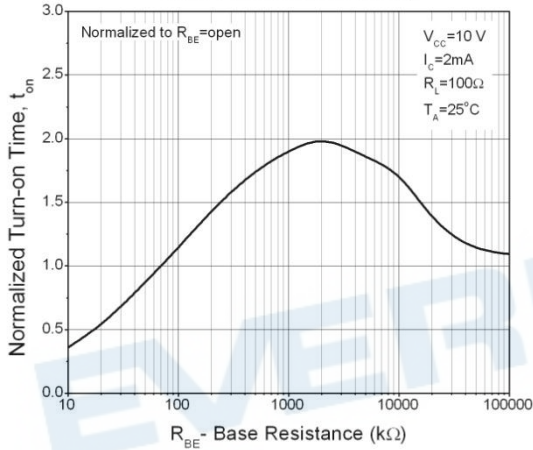


Figure 10. Turn-off Time vs Base-Emitter Resistance

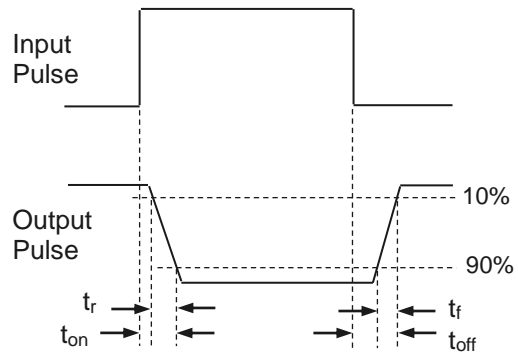
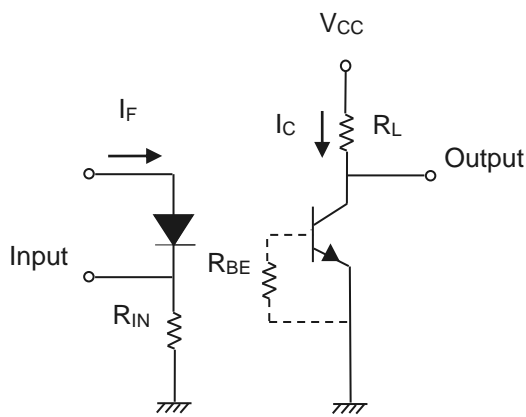
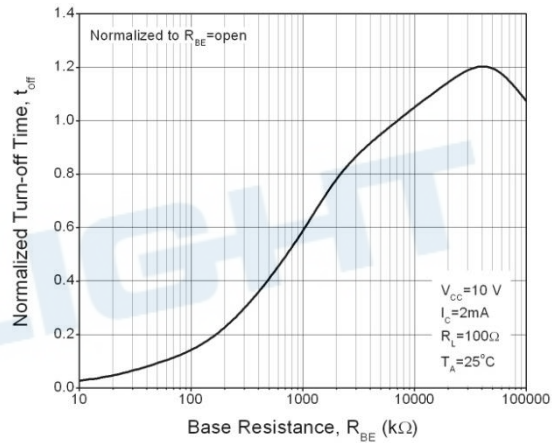


Figure 11. Switching Time Test Circuit & Waveforms

## Order Information

### Part Number

**CNY17-XY(Z)-V**

or

**CNY17F-XY(Z)-V**

### Note

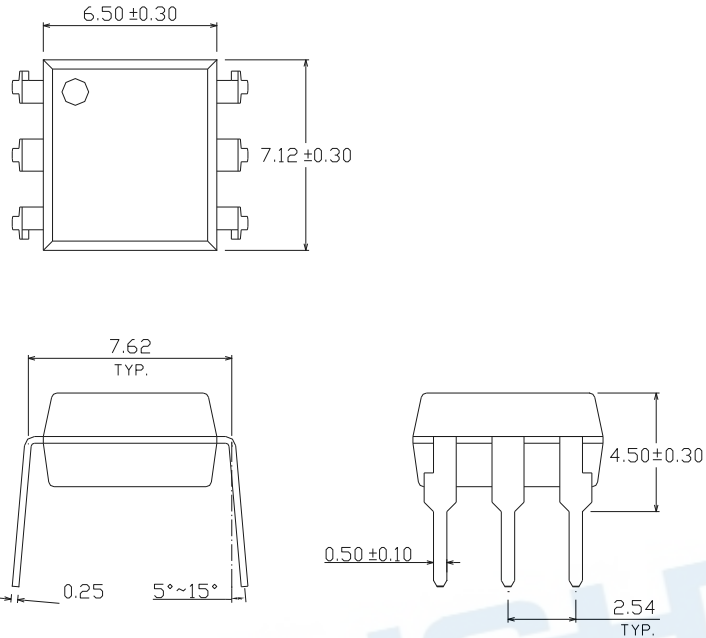
- X = Part no. (1, 2, 3 or 4)
- Y = Lead form option (S, S1, M or none)
- Z = Tape and reel option (TA, TB or none).
- V = VDE (optional)

Option	Description	Packing quantity
None	Standard DIP-6	65 units per tube
M	Wide lead bend (0.4 inch spacing)	65 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel

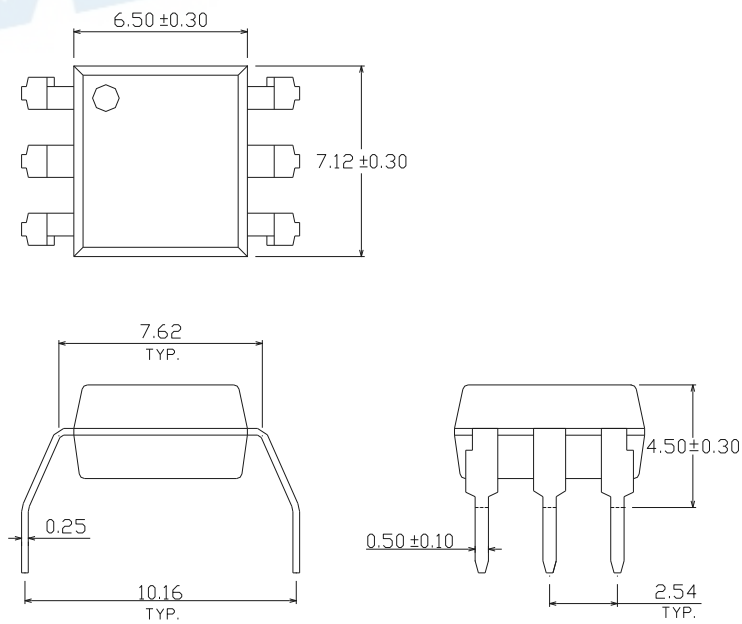


Package Dimension (Dimensions in mm)

Standard DIP Type

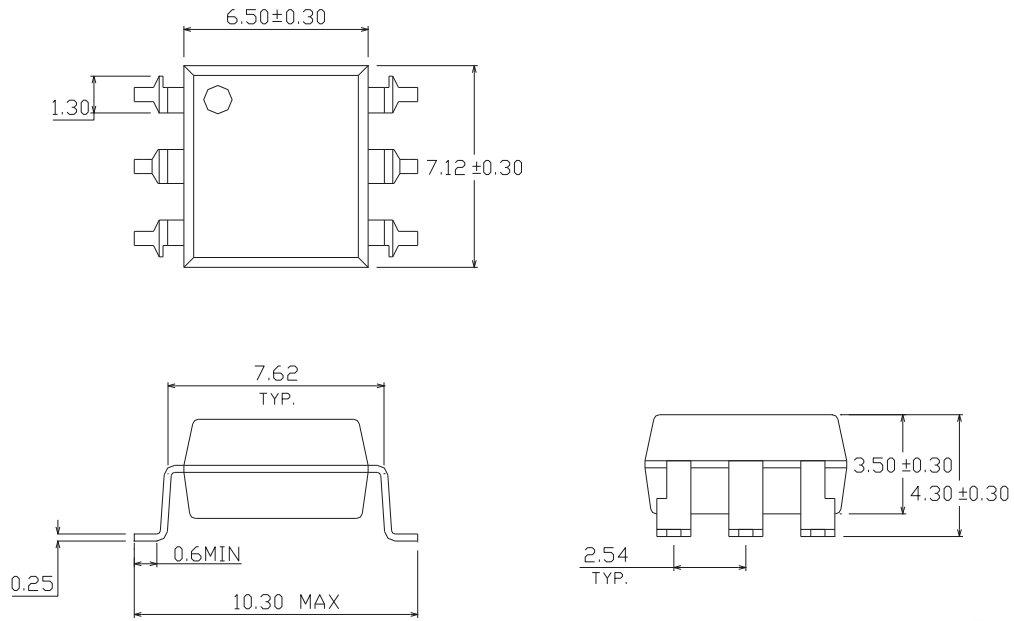


Option M Type

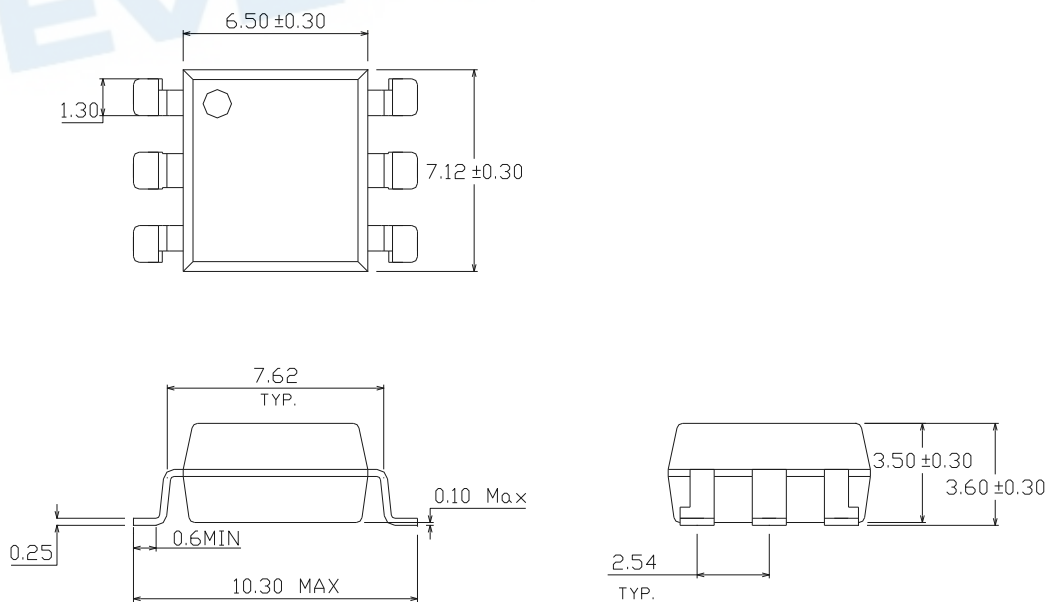




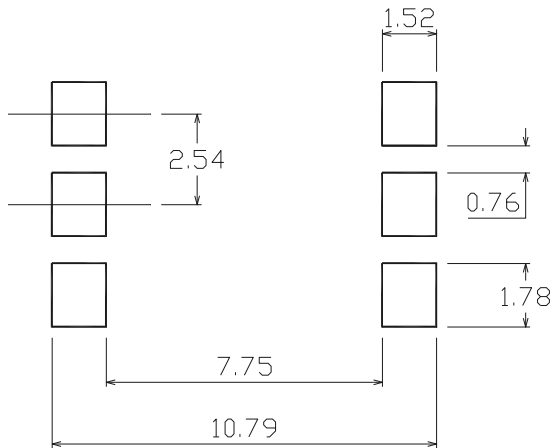
Option S Type



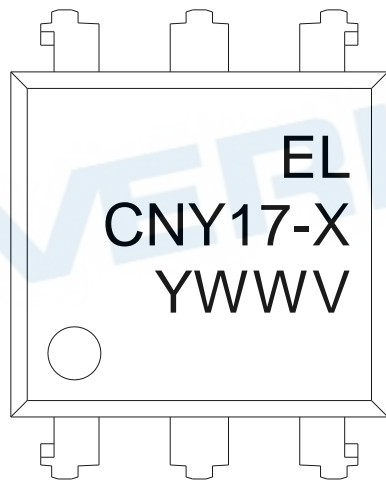
Option S1 Type



### Recommended pad layout for surface mount leadform



### Device Marking

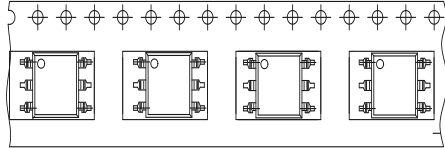


### Notes

- EL denotes Everlight
- CNY17-X denotes Device Number (X: 1, 2, 3 or 4)
- Y denotes 1 digit Year code
- WW denotes 2 digit Week code
- V denotes VDE (optional)

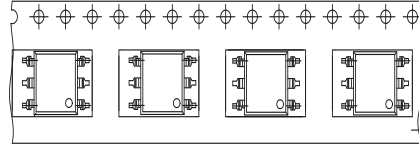
**Tape & Reel Packing Specifications**

**Option TA**



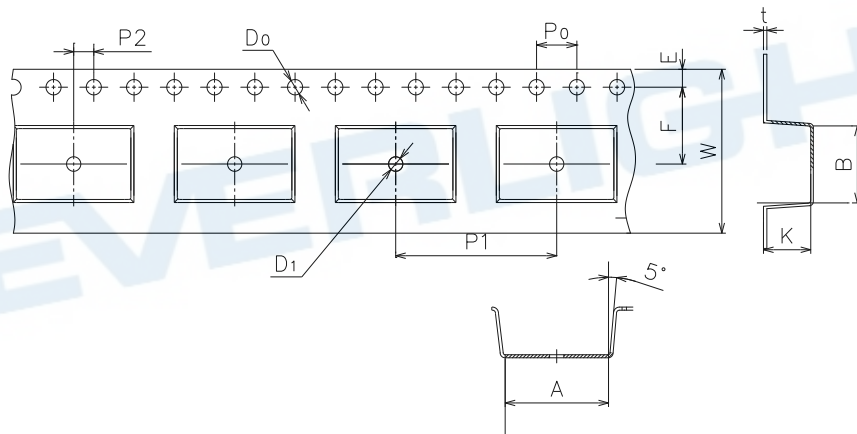
Direction of feed from reel

**Option TB**



Direction of feed from reel

**Tape dimensions**

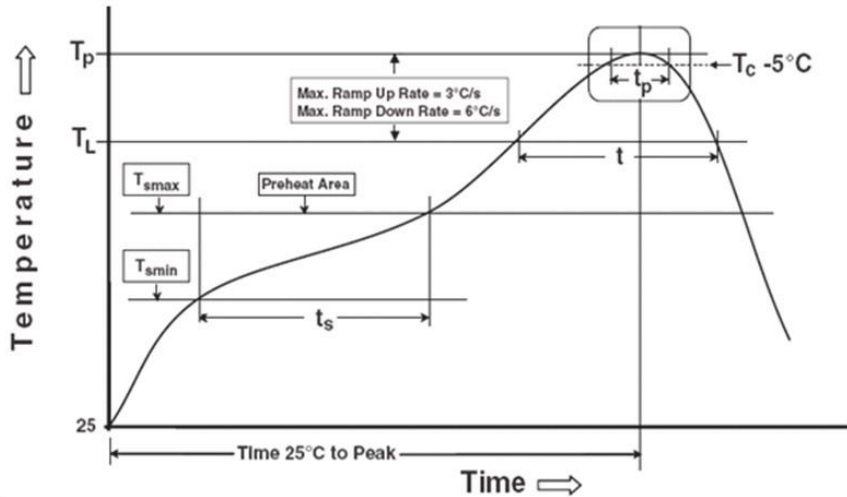


Dimension No.	<b>A</b>	<b>B</b>	<b>Do</b>	<b>D1</b>	<b>E</b>	<b>F</b>
Dimension (mm)	10.8±0.1	7.5±0.1	1.5±0.1	1.5+0.1/-0	1.75±0.1	7.5±0.1
Dimension No.	<b>Po</b>	<b>P1</b>	<b>P2</b>	<b>t</b>	<b>W</b>	<b>K</b>
Dimension (mm)	4.0±0.15	12±0.1	2.0±0.1	0.35±0.03	16.0±0.2	4.5±0.1

## Precautions for Use

### 1. Soldering Condition

#### 1.1 (A) Maximum Body Case Temperature Profile for evaluation of Reflow Profile



Note:

Reference: IPC/JEDEC J-STD-020D

#### Preheat

Temperature min ( $T_{smin}$ )	150 °C
Temperature max ( $T_{smax}$ )	200°C
Time ( $T_{smin}$ to $T_{smax}$ ) ( $t_s$ )	60-120 seconds
Average ramp-up rate ( $T_{smax}$ to $T_p$ )	3 °C/second max

#### Other

Liquidus Temperature ( $T_L$ )	217 °C
Time above Liquidus Temperature ( $t_L$ )	60-100 sec
Peak Temperature ( $T_p$ )	260°C
Time within 5 °C of Actual Peak Temperature: $T_p - 5^\circ C$	30 s
Ramp- Down Rate from Peak Temperature	6°C /second max.
Time 25°C to peak temperature	8 minutes max.
Reflow times	3 times